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Kind regards,

Team Nexperia

NPN/NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

Rev. 04 — 18 May 2005

Product data sheet

1. Product profile

1.1 General description

NPN/NPN Resistor-Equipped Transistors (RET).

Type number	Package		NPN/PNP	PNP/PNP	
	Philips	JEITA	complement	complement	
PEMH24	SOT666	-	PEMD24	PEMB24	
PUMH24	SOT363	SC-88	PUMD24	PUMB24	

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
lo	output current (DC)		-	-	20	mA
R1	bias resistor 1 (input)		70	100	130	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



NPN/NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

2. Pinning information

Table 3:	Pinning		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

3. Ordering information

Table 4: Ordering information					
Type number	Package				
	Name	Description	Version		
PEMH24	-	plastic surface mounted package; 6 leads	SOT666		
PUMH24	SC-88	plastic surface mounted package; 6 leads	SOT363		

4. Marking

Table 5: Marking codes	
Type number	Marking code ^[1]
PEMH24	6T
PUMH24	H8*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

1 | 2 3 *sym063*

NPN/NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transi	stor				
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-10	V
lo	output current (DC)		-	20	mA
I _{СМ}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		<u>[1][2]</u> _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1][2] _	300	mW

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

NPN/NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

6. Thermal characteristics

Table 7:	Thermal characteristics	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Per trans	istor						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air					
	SOT363		<u>[1]</u> -	-	625	K/W	
	SOT666		[1][2] _	-	625	K/W	
Per devic	e						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air					
	SOT363		<u>[1]</u> -	-	416	K/W	
	SOT666		<u>[1][2]</u> _	-	416	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8: Characteristics

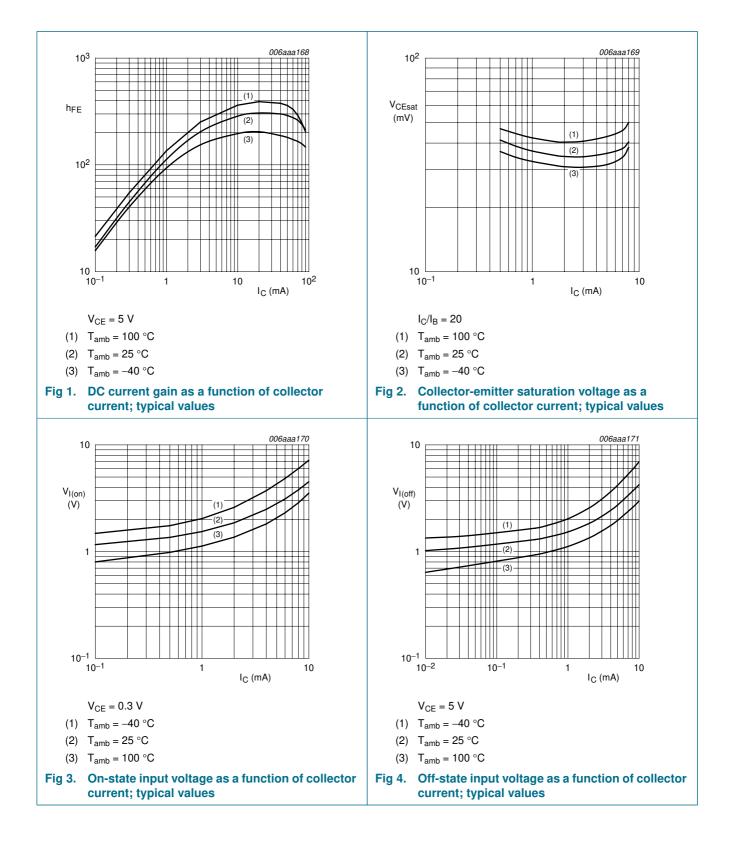
 $T_{amb} = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Tun	Max	Unit
Symbol	Parameter	Conditions	IVIIA	Тур	Max	Unit
Per transis	stor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$	-	-	1	μA
	cut-off current	$\label{eq:VCE} \begin{array}{l} V_{CE}=30 \text{ V}; \text{ I}_{B}=0 \text{ A}; \\ T_{j}=150 \ ^{\circ}\text{C} \end{array}$	-	- 50		μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	50	μA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 5 \text{ mA}$	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 5 mA; I _B = 0.25 mA	-	-	150	mV
V _{I(off)}	off-state input voltage	$V_{CE}=5~V;~I_{C}=100~\mu A$	-	1.1	0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 1 \text{ mA}$	3	1.5	-	V
R1	bias resistor 1 (input)		70	100	130	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = 10 \; V; \ I_E = i_e = 0 \; A; \\ f = 1 \; MHz \end{array}$	-	-	2.5	pF

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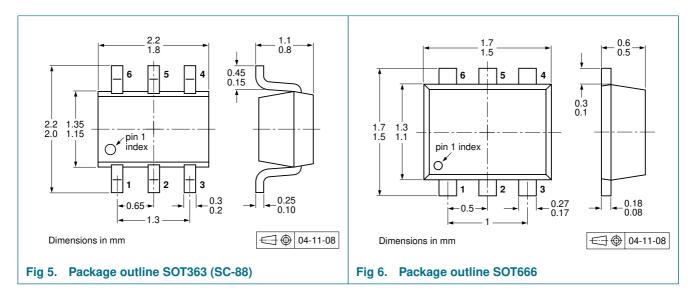
PEMH24; PUMH24

NPN/NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω



NPN/NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

8. Package outline



9. Packing information

Table 9: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packi	ng quai	ntity	
				3000	4000	8000	10000
PEMH24	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMH24 SOT363		4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

[1] For further information and the availability of packing methods, see Section 15.

[2] T1: normal taping

[3] T2: reverse taping

NPN/NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

10. Revision history

Table 10:Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PEMH24_PUMH24_4	20050518	Product data sheet	-	9397 750 14456	PUMH24_3
Modifications:	Type PEMH24 added				
	 Table 1 "Pi 	roduct overview": addee	d		
	• Figure 1, 2	2, <u>3</u> and <u>4</u> : electrical gra	phs added		
	 <u>Table 9 "Pa</u> 	acking methods": addeo	d		
	Section 14	"Trademarks": added			
PUMH24_3	20041015	Product data sheet	-	9397 750 13628	PUMH24_2
PUMH24_2	20040414	Product specification	-	9397 750 13087	PUMH24_1
PUMH24_1	20031016	Product specification	-	9397 750 11895	-

NPN/NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

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Level	Data sheet status [1]	Product status [2] [3]	Definition
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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PEMH24; PUMH24

NPN/NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

16. Contents

1	Product profile 1
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 4
7	Characteristics 4
8	Package outline 6
9	Packing information 6
10	Revision history7
11	Data sheet status 8
12	Definitions 8
13	Disclaimers 8
14	Trademarks 8
15	Contact information8



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Published in The Netherlands

Date of release: 18 May 2005 Document number: 9397 750 14456